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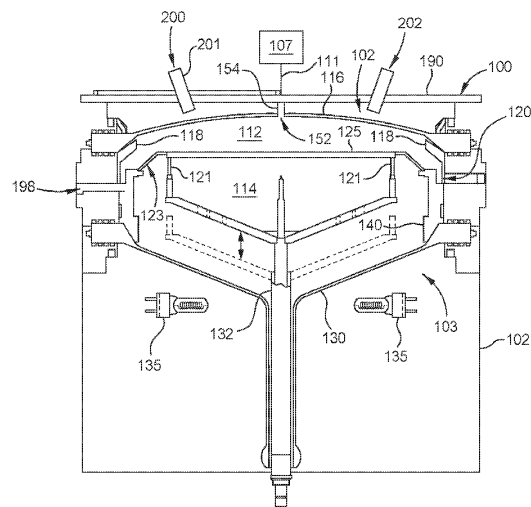


FIG. 1

(57) Abstract: The present invention provides methods and apparatus for processing semiconductor substrates in an epitaxy chamber configured to map a temperature profile for both substrates and interior chamber components. In one embodiment, the semiconductor processing chamber has a body having ceiling and a lower portion defining an interior volume. A substrate support is disposed in the interior volume. A mounting plate is coupled to the ceiling outside the interior volume. A movement assembly is coupled to the mounting plate. A sensor is coupled to the movement assembly and moveable relative to the ceiling. The sensor is configured to detect a temperature location in the interior volume.

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